

# SILICON DIODE

## DESCRIPTION:

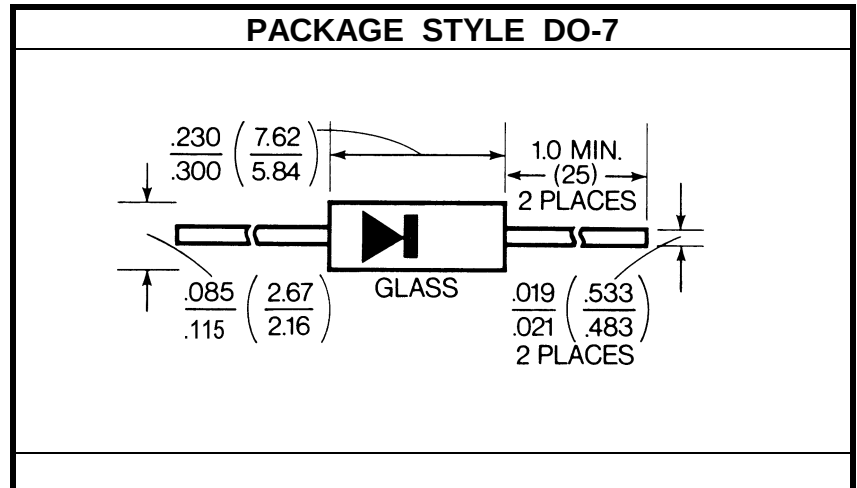
The **ASI FH1100** is a Silicon Diffused Hot Carrier Diode.

## FEATURES INCLUDE:

- $Q_S = 1.6$  pC Typ.
- $C = 1.0$  pF Max. @  $f = 890$  MHz
- Hermetic Glass Package

## MAXIMUM RATINGS

|                 |                        |
|-----------------|------------------------|
| $I_F$           | 10 mA                  |
| $V_R$           | 5.0 V                  |
| $P_{DISS}$      | 100 mW @ $T_C = 25$ °C |
| $T_J$           | -65 °C to +125 °C      |
| $T_{STG}$       | -65 °C to +150 °C      |
| $T_{soldering}$ | +260 °C for 5 Seconds  |



## CHARACTERISTICS $T_C = 25$ °C

| SYMBOL   | TEST CONDITIONS     | MINIMUM | TYPICAL | MAXIMUM | UNITS   |
|----------|---------------------|---------|---------|---------|---------|
| $V_F$    | $I_F = 10$ mA       |         |         | 550     | mV      |
| $I_R$    | $V_R = 1.0$ V       |         |         | 1.0     | $\mu$ A |
| $V_{BR}$ | $I_R = 100$ $\mu$ A | 5.0     |         |         | V       |
| $C_{T0}$ | $V_R = 0$ V         |         | 1.0     |         | pF      |
| $NF$     |                     |         |         | 10      | dB      |
| $Q_S$    | $I_F = 10$ mA       |         | 1.6     |         | pC      |